

MJE5850, MJE5851, MJE5852

Switch-mode Series PNP Silicon Power Transistors

The MJE5850, MJE5851 and the MJE5852 transistors are designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.

Features

- Switching Regulators
- Inverters
- Solenoid and Relay Drivers
- Motor Controls
- Deflection Circuits
- Fast Turn-Off Times
- Operating Temperature Range -65 to $+150^{\circ}\text{C}$
- 100°C Performance Specified for:
 - ◆ Reversed Biased SOA with Inductive Loads
 - ◆ Switching Times with Inductive Loads
 - ◆ Saturation Voltages
 - ◆ Leakage Currents
- Complementary to the MJE13007 Series
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|--------------------------------|-------------------|----------------------------|
| Collector-Emitter Voltage MJE5850 MJE5851 MJE5852 | $V_{\text{CEO(sus)}}$ | 300 350 400 | Vdc |
| Collector-Emitter Voltage MJE5850 MJE5851 MJE5852 | V_{CEV} | 350 400 450 | Vdc |
| Emitter Base Voltage | V_{EB} | 6.0 | Vdc |
| Collector Current – Continuous (Note 1) | I_{C} | 8.0 | Adc |
| Collector Current – Peak (Note 1) | I_{CM} | 16 | Adc |
| Base Current – Continuous (Note 1) | I_{B} | 4.0 | Adc |
| Base Current – Peak (Note 1) | I_{BM} | 8.0 | Adc |
| Total Power Dissipation @ $T_{\text{C}} = 25^{\circ}\text{C}$ Derate above 25°C | P_{D} | 80 0.640 | W W/ $^{\circ}\text{C}$ |
| Operating and Storage Junction Temperature Range | $T_{\text{J}}, T_{\text{stg}}$ | -65 to 150 | $^{\circ}\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.

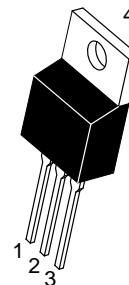
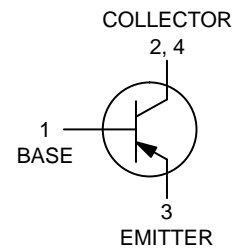
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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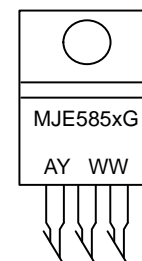
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**8 AMPERE
PCP SILICON
POWER TRANSISTORS
300–350–400 VOLTS
80 WATTS**



TO-220
CASE 221A-09
STYLE 1

MARKING DIAGRAM



MJE585x = Device Code
x = 0, 1, or 2
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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THERMAL CHARACTERISTICS

| Rating | Symbol | Max | Unit |
|---|-----------------|------|---------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 1.25 | $^{\circ}C/W$ |
| Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds | T_L | 275 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|---|----------------|-------------------|-------------|-------------|------|
| Collector-Emitter Sustaining Voltage ($I_C = 10\text{ mA}$, $I_B = 0$) MJE5850 MJE5851 MJE5852 | $V_{CEO(sus)}$ | 300 350 400 | - - - | - - - | Vdc |
| Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 100^{\circ}C$) | I_{CEV} | - - | - - | 0.5 2.5 | mAdc |
| Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEV}$, $R_{BE} = 50\ \Omega$, $T_C = 100^{\circ}C$) | I_{CER} | - | - | 3.0 | mAdc |
| Emitter Cutoff Current ($V_{EB} = 6.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | - | - | 1.0 | mAdc |

SECOND BREAKDOWN

| | | | | | |
|---|-----------|---------------|--|--|--|
| Second Breakdown Collector Current with base forward biased | $I_{S/b}$ | See Figure 12 | | | |
| Clamped Inductive SOA with base reverse biased | RBSOA | See Figure 13 | | | |

ON CHARACTERISTICS (Note 2)

| | | | | | |
|--|---------------|-------------|-------------|-------------------|-----|
| DC Current Gain ($I_C = 2.0\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 5.0\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) | h_{FE} | 15 5 | - - | - - | - |
| Collector-Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$) ($I_C = 8.0\text{ Adc}$, $I_B = 3.0\text{ Adc}$) ($I_C = 4.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$, $T_C = 100^{\circ}C$) | $V_{CE(sat)}$ | - - - | - - - | 2.0 5.0 2.5 | Vdc |
| Base-Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$) ($I_C = 4.0\text{ Adc}$, $I_B = 1.0\text{ Adc}$, $T_C = 100^{\circ}C$) | $V_{BE(sat)}$ | - - | - - | 1.5 1.5 | Vdc |

DYNAMIC CHARACTERISTICS

| | | | | | |
|--|----------|---|-----|---|----|
| Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 1.0\text{ kHz}$) | C_{ob} | - | 270 | - | pF |
|--|----------|---|-----|---|----|

SWITCHING CHARACTERISTICS

| Resistive Load (Table 1) | | | | | | |
|-----------------------------------|--|----------|---|-------|-----|---------------|
| Delay Time | ($V_{CC} = 250\text{ Vdc}$, $I_C = 4.0\text{ A}$, $I_{B1} = 1.0\text{ A}$, $t_p = 50\ \mu\text{s}$, Duty Cycle $\leq 2\%$) | t_d | - | 0.025 | 0.1 | μs |
| Rise Time | | t_r | - | 0.100 | 0.5 | μs |
| Storage Time | ($V_{CC} = 250\text{ Vdc}$, $I_C = 4.0\text{ A}$, $I_{B1} = 1.0\text{ A}$, $V_{BE(off)} = 5\text{ Vdc}$, $t_p = 50\ \mu\text{s}$, Duty Cycle $\leq 2\%$) | t_s | - | 0.60 | 2.0 | μs |
| Fall Time | | t_f | - | 0.11 | 0.5 | μs |
| Inductive Load, Clamped (Table 1) | | | | | | |
| Storage Time | ($I_{CM} = 4\text{ A}$, $V_{CEM} = 250\text{ V}$, $I_{B1} = 1.0\text{ A}$, $V_{BE(off)} = 5\text{ Vdc}$, $T_C = 100^{\circ}C$) | t_{sv} | - | 0.8 | 3.0 | μs |
| Crossover Time | | t_c | - | 0.4 | 1.5 | μs |
| Fall Time | | t_{fi} | - | 0.1 | - | μs |
| Storage Time | ($I_{CM} = 4\text{ A}$, $V_{CEM} = 250\text{ V}$, $I_{B1} = 1.0\text{ A}$, $V_{BE(off)} = 5\text{ Vdc}$, $T_C = 25^{\circ}C$) | t_{sv} | - | 0.5 | - | μs |
| Crossover Time | | t_c | - | 0.125 | - | μs |
| Fall Time | | t_{fi} | - | 0.1 | - | μs |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: PW = 300 μs . Duty Cycle $\leq 2\%$

TYPICAL ELECTRICAL CHARACTERISTICS

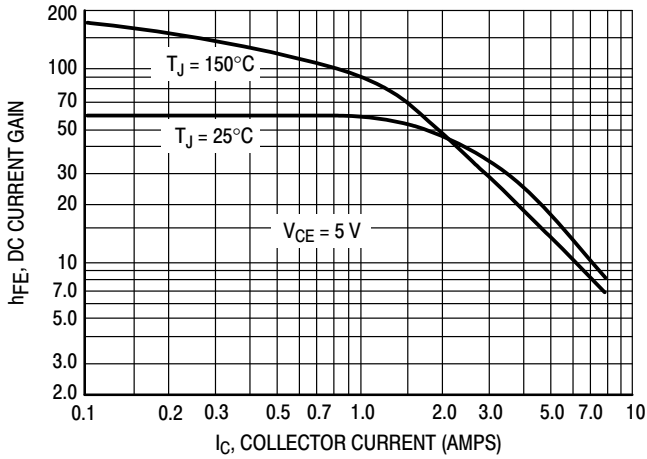


Figure 1. DC Current Gain

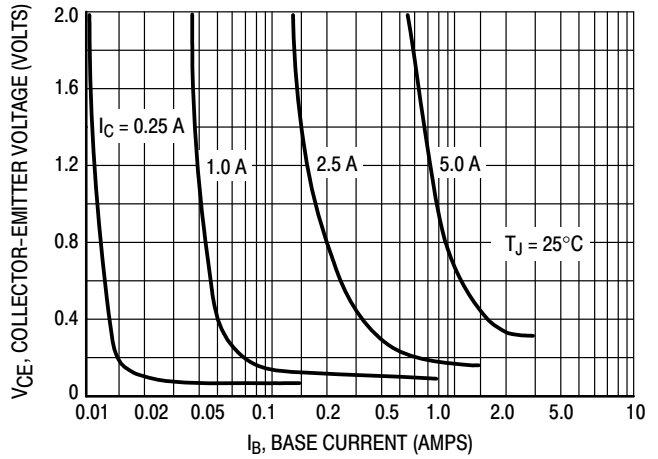


Figure 2. Collector Saturation Region

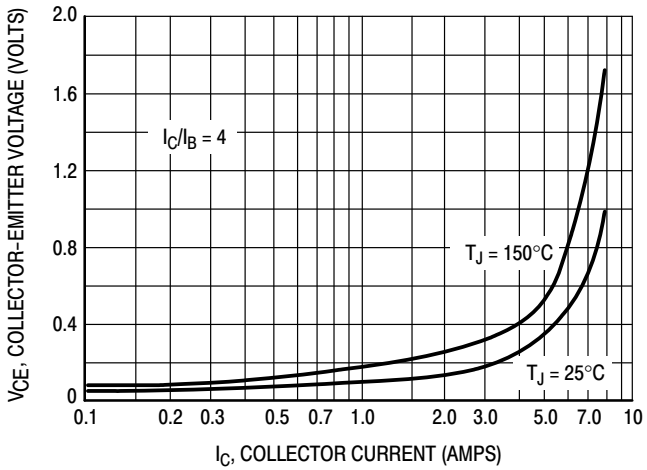


Figure 3. Collector-Emitter Saturation Voltage

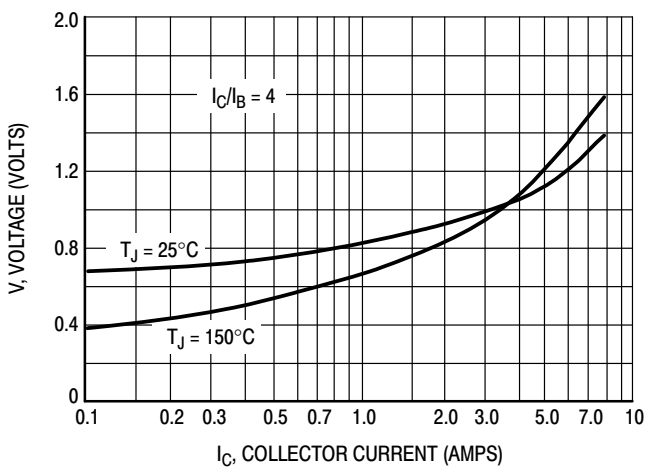


Figure 4. Base-Emitter Voltage

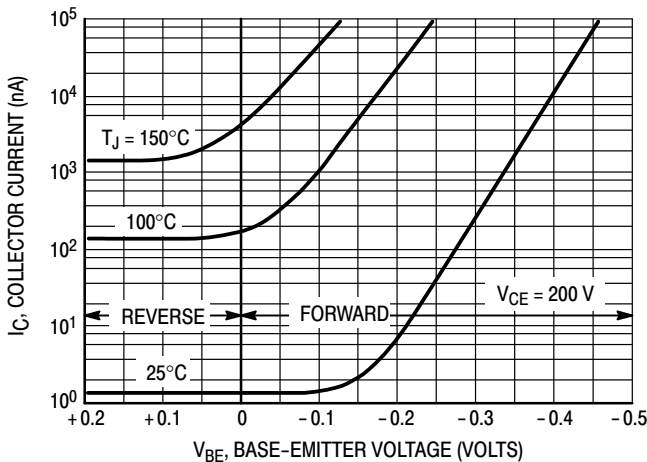


Figure 5. Collector Cutoff Region

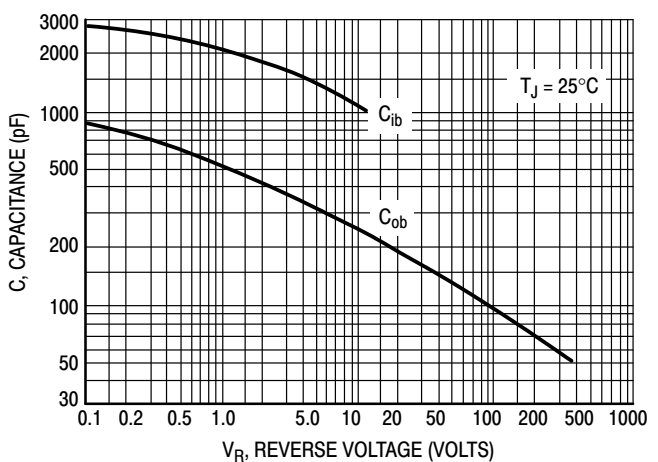
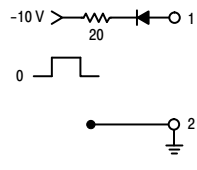
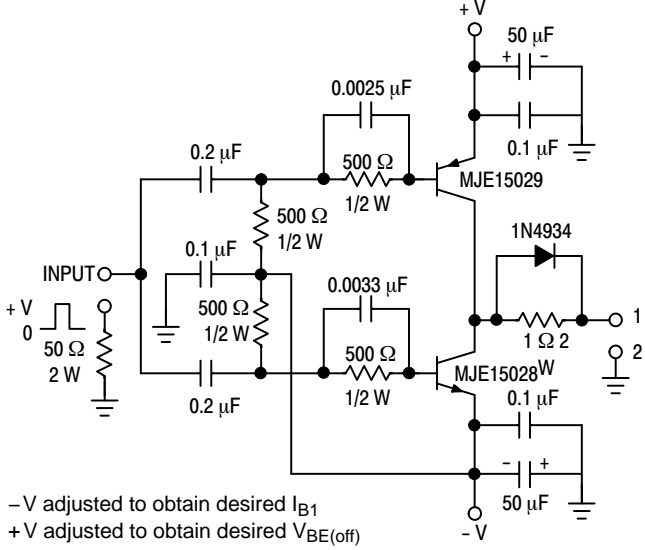
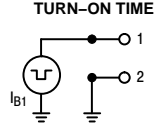
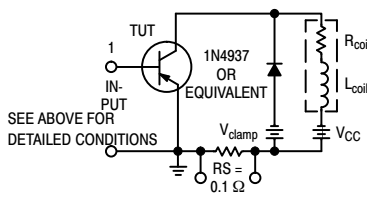
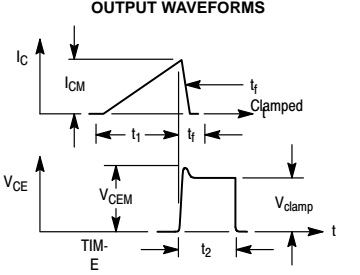
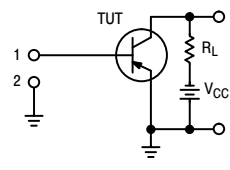


Figure 6. Capacitance

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Table 1. TEST CONDITIONS FOR DYNAMIC PERFORMANCE

| | $V_{CEO(sus)}$ | RBSOA AND INDUCTIVE SWITCHING | RESISTIVE SWITCHING |
|------------------|--|--|--|
| INPUT CONDITIONS |  <p>PW Varied to Attain $I_C = 100 \text{ mA}$</p> |  <p>-V adjusted to obtain desired I_{B1} +V adjusted to obtain desired $V_{BE(off)}$</p> |  <p>TURN-ON TIME</p> <p>I_{B1} adjusted to obtain the forced η_{FE} desired</p> <p>TURN-OFF TIME</p> <p>Use inductive switching driver as the input to the resistive test circuit.</p> |
| CIRCUIT VALUES | $L_{coil} = 80 \text{ mH}$, $V_{CC} = 10 \text{ V}$ $R_{coil} = 0.7 \Omega$ | $L_{coil} = 180 \mu\text{H}$ $R_{coil} = 0.05 \Omega$ $V_{CC} = 20 \text{ V}$ $V_{clamp} = 250 \text{ V}$ R_B adjusted to attain desired I_{B1} | $V_{CC} = 250 \text{ V}$ $R_L = 62 \Omega$ Pulse Width = 10 μs |
| TEST CIRCUITS | <p>INDUCTIVE TEST CIRCUIT</p>  <p>SEE ABOVE FOR DETAILED CONDITIONS</p> | <p>OUTPUT WAVEFORMS</p>  <p>t_1 Adjusted to Obtain I_C</p> $t_1 \approx \frac{L_{coil} (I_{CM})}{V_{CC}}$ $t_2 \approx \frac{L_{coil} (I_{CM})}{V_{Clamp}}$ <p>Test Equipment Scope — Tektronix 475 or Equivalent</p> | <p>RESISTIVE TEST CIRCUIT</p>  |

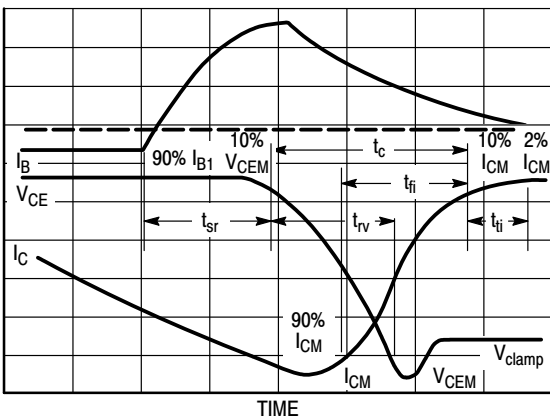


Figure 7. Inductive Switching Measurements

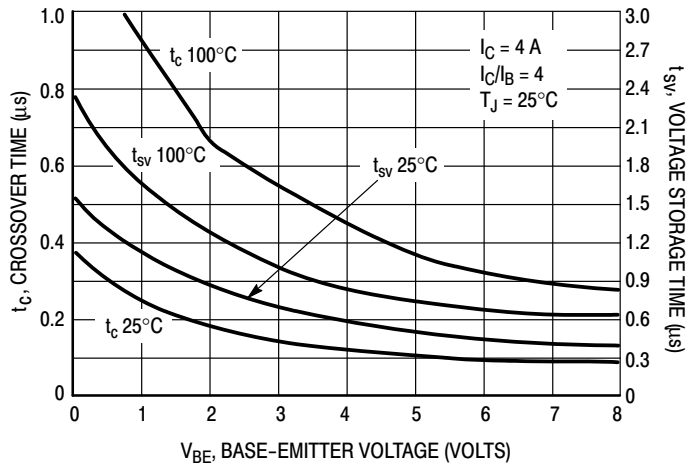


Figure 8. Inductive Switching Times

SWITCHING TIMES NOTE

In resistive switching circuits, rise, fall, and storage times have been defined and apply to both current and voltage waveforms since they are in phase. However, for inductive loads which are common to SWITCHMODE power supplies and hammer drivers, current and voltage waveforms are not in phase. Therefore, separate measurements must be made on each waveform to determine the total switching time. For this reason, the following new terms have been defined.

- t_{SV} = Voltage Storage Time, 90% I_{B1} to 10% V_{CEM}
- t_{RV} = Voltage Rise Time, 10–90% V_{CEM}
- t_{fi} = Current Fall Time, 90–10% I_{CM}
- t_{ti} = Current Tail, 10–2% I_{CM}
- t_c = Crossover Time, 10% V_{CEM} to 10% I_{CM}

An enlarged portion of the inductive switching waveform is shown in Figure 7 to aid on the visual identity of these terms.

For the designer, there is minimal switching loss during storage time and the predominant switching power losses occur during the crossover interval and can be obtained using the standard equation from AN-222A:

$$P_{SWT} = 1/2 V_{CC} I_C(t_c) f$$

In general, $t_{RV} + t_{fi} \approx t_c$. However, at lower test currents this relationship may not be valid.

As is common with most switching transistors, resistive switching is specified at 25°C and has become a benchmark for designers. However, for designers of high frequency converter circuits, the user oriented specifications which make this a “SWITCHMODE” transistor are the inductive switching speeds (t_c and t_{SV}) which are guaranteed at 100°C.

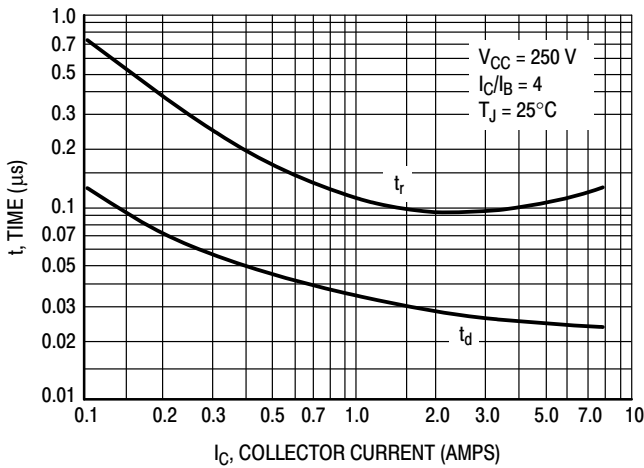


Figure 9. Turn-On Switching Times

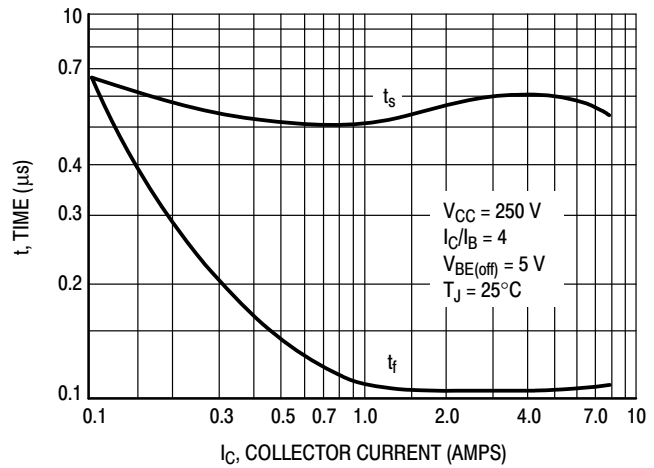


Figure 10. Turn-Off Switching Time

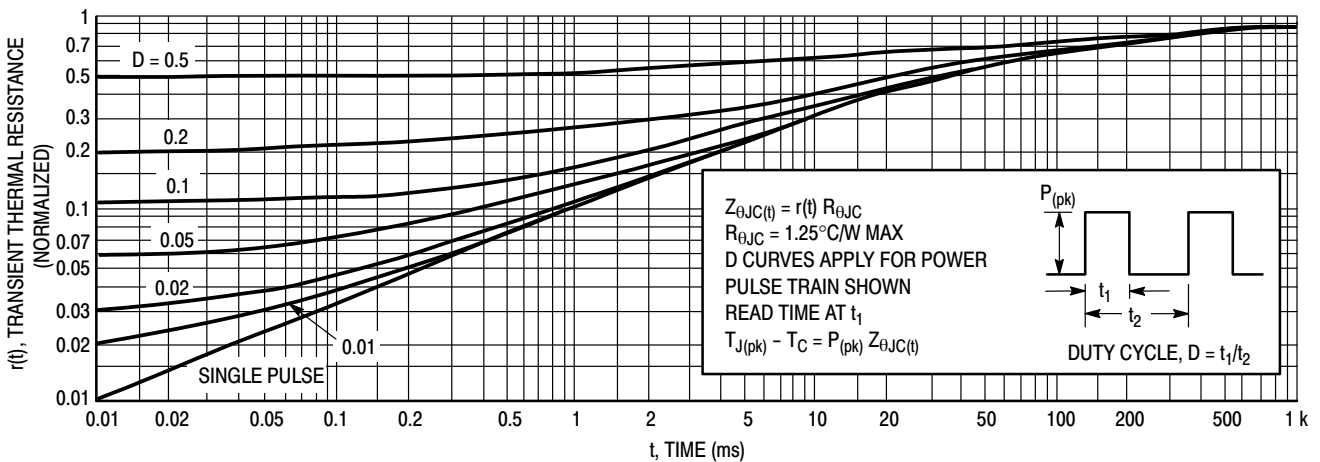


Figure 11. Typical Thermal Response [$Z_{\theta JC}(t)$]

MJE5850, MJE5851, MJE5852

The Safe Operating Area figures shown in Figures 12 and 13 are specified for these devices under the test conditions shown.

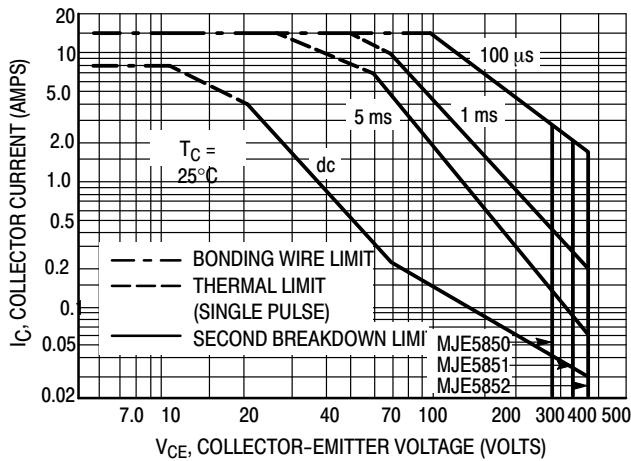


Figure 12. Maximum Forward Bias Safe Operating Area

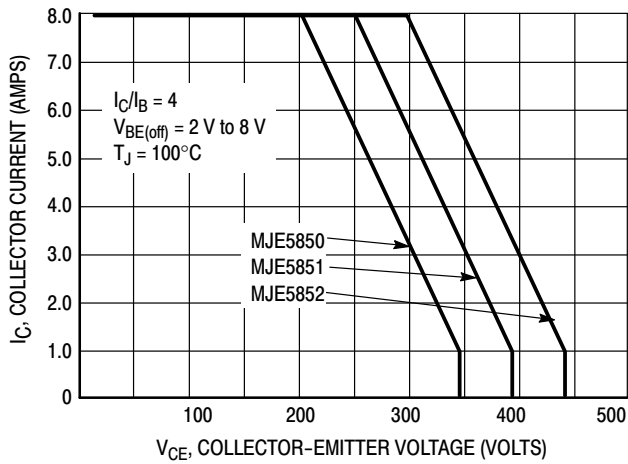


Figure 13. RBSOA, Maximum Reverse Bias Safe Operating Area

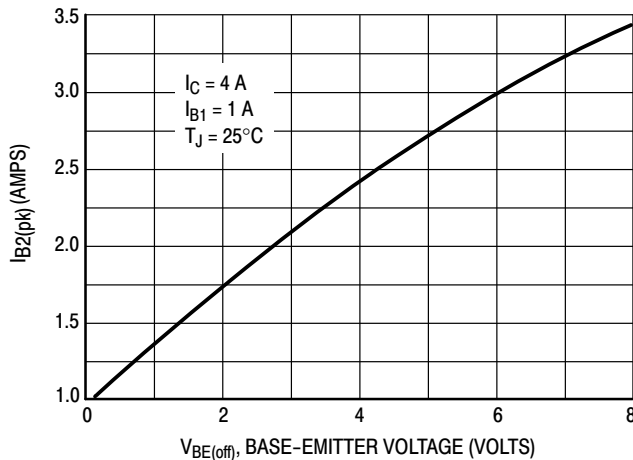


Figure 14. Peak Reverse Base Current

Safe Operating Area Information

Forward Bias

There are two limitations on the power handling ability of a transistor average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 12 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 12 may be found at any case temperature by using the appropriate curve on Figure 15.

$T_{J(pk)}$ may be calculated from the data in Figure 11. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Reverse Bias

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current condition allowable during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 13 gives the RBSOA characteristics.

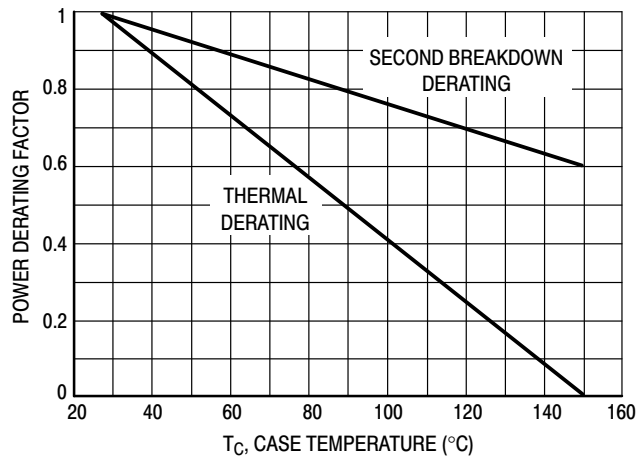


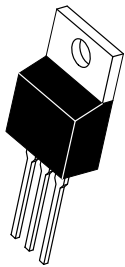
Figure 15. Forward Bias Power Derating

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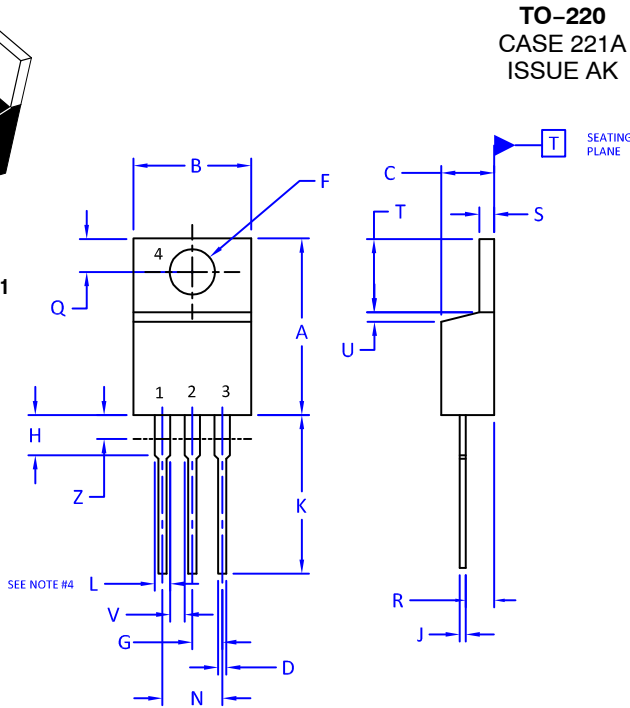
ORDERING INFORMATION

| Device | Package | Shipping |
|----------|---------------------|-----------------|
| MJE5850G | TO-220 (Pb-Free) | 50 Units / Rail |
| MJE5851G | TO-220 (Pb-Free) | 50 Units / Rail |
| MJE5852G | TO-220 (Pb-Free) | 50 Units / Rail |

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1



TO-220
CASE 221A
ISSUE AK

DATE 13 JAN 2022

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.415 | 9.66 | 10.53 |
| C | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.60 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.41 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

| | | |
|------------------|-------------|--|
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North American Technical Support:
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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

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For additional information, please contact your local Sales Representative

